AG246SN060MPF

N-Channel Enhancement Mode MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60V	1.5mΩ@10V	246A

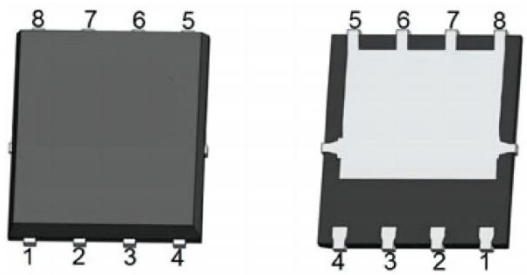
Feature

- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Application

- Power switching application
- Uninterruptible power supply
- DC-DC convertor

Package



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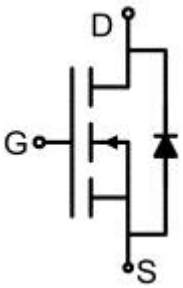
Circuit diagram



Marking

Absolute maximum ratings (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current[1, 3](V_{GS} =10V, Chip limitation)	I_D	246	A
Continuous Drain Current[1, 3](V_{GS} =10V,T_C =100℃)	I_D(100℃)	173	A
Pulsed Drain Current (t_p ≤10μs)	I_{DM}	667	A
Single Pulse Avalanche Energy[2]	E_{AS}	841	mJ
Power Dissipation[1, 3]	P_D	176.4	W
Thermal Resistance Junction to Case	$R_{\theta JC}$	0.85	℃/W
Operating Junction Temperature	T_J	-55 ~ +175	℃
Storage Temperature	T_{STG}	-55 ~ +175	℃

Electrical characteristics (T_J =25 ℃, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} =0V, I_D =1mA	60			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =48V, V_{GS} =0V			1	μA
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±20V			±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	1.3	1.7	2.3	V
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =50A		1.15	1.5	mΩ
Dynamic characteristics[4]						
Input Capacitance	C_{iss}	V_{DS} =30V, V_{GS} =0V, f =1MHz		6331		pF
Output Capacitance	C_{oss}			1681		
Reverse Transfer Capacitance	C_{rss}			212		
Total Gate Charge	Q_g	V_{DS} =30V, V_{GS} =10V, I_D =50A		114		nC
Gate-Source Charge	Q_{gs}			20.1		
Gate-Drain Charge	Q_{gd}			23.2		
Turn-on delay time	$t_{d(on)}$	V_{DS} =30V, V_{GS}=10V, I_D =50A R_G =3Ω		16.9		nS
Turn-on rise time	t_r			97.7		
Turn-off delay time	$t_{d(off)}$			105.2		
Turn-off fall time	t_f			123.8		
Source-Drain Diode characteristics						
Diode Forward Current	I_S				246	A
Diode Forward voltage	V_{SD}	V_{GS} =0V, I_S =50A			1.2	V
Reverse Recovery Time	T_{rr}	V_{GS} =0V, V_R=30V, I_F =50A di/dt =-100A/μs		34.6		nS
Reverse Recovery Charge	Q_{rr}			27.7		nC

Notes:

1) The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

2) T_J =25℃, V_G =10V, R_G =25Ω, L =0.5mH, I_{AS} =58A.

3) Thermal resistance from junction to soldering point (on the exposed drain pad).

4) Guaranteed by design, not subject to production testing.

Typical Characteristics

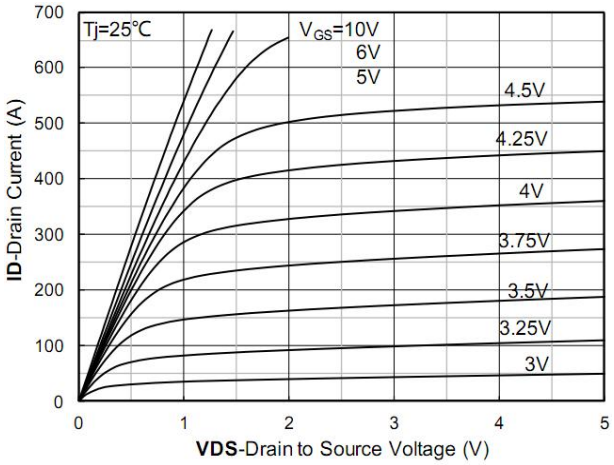


Figure 1. Output Characteristics; typical values

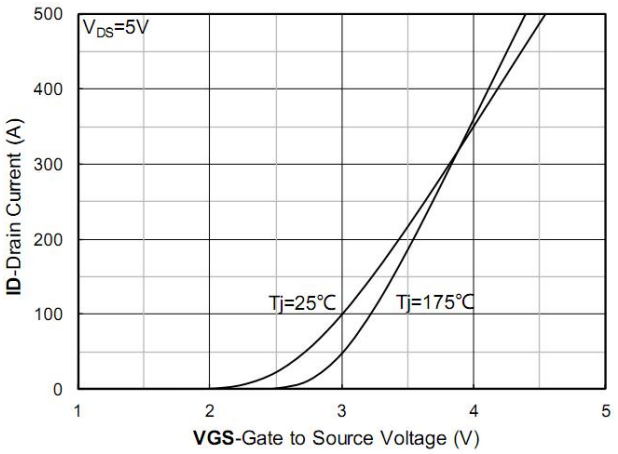


Figure 2. Transfer Characteristics; typical values

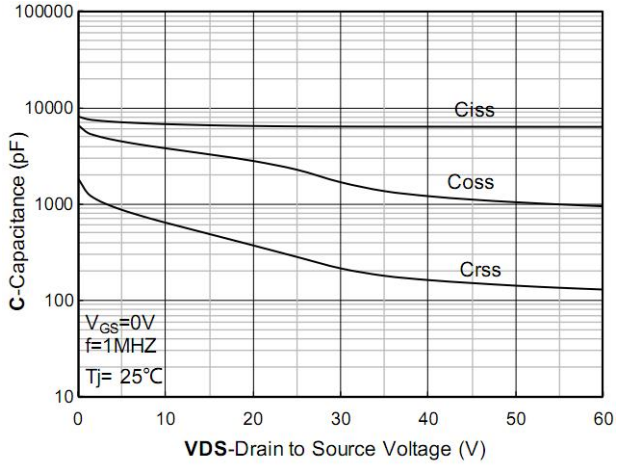


Figure 3. Capacitance Characteristics; typical values

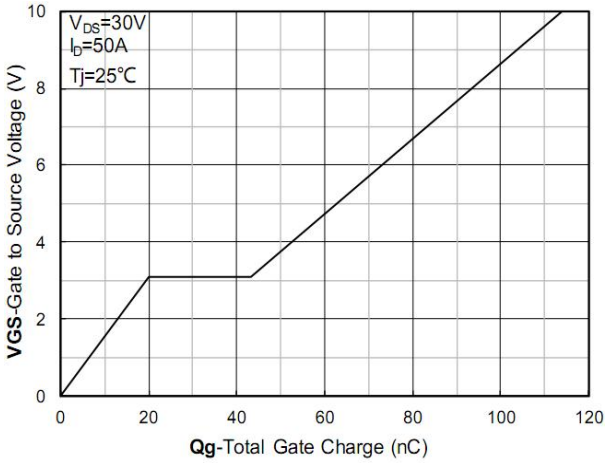


Figure 4. Gate Charge; typical values

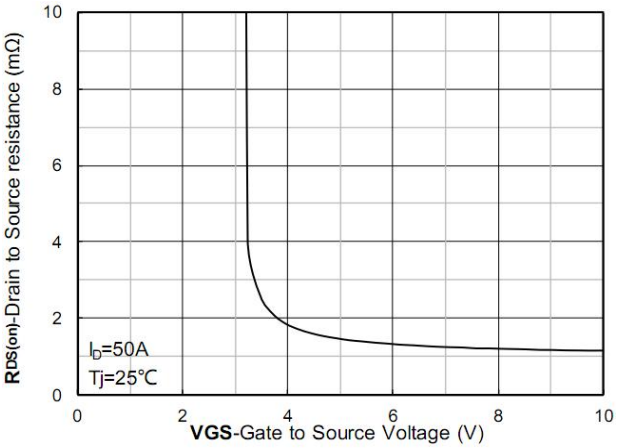


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

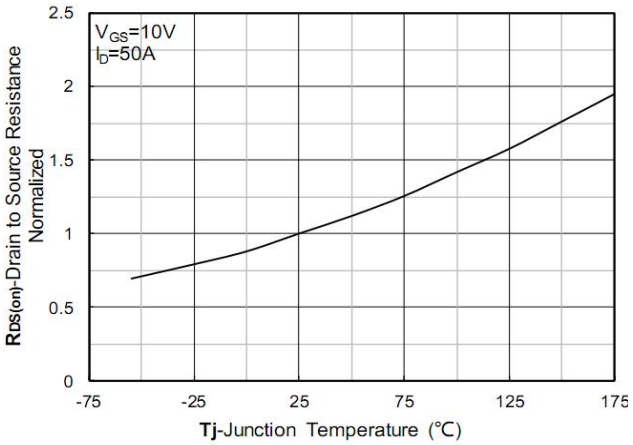


Figure 6. Normalized On-Resistance

Typical Characteristics

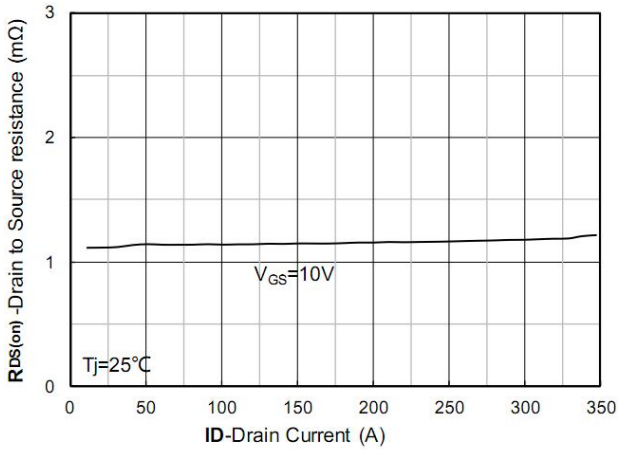


Figure 7. $R_{DS(on)}$ vs. Drain Current; typical values

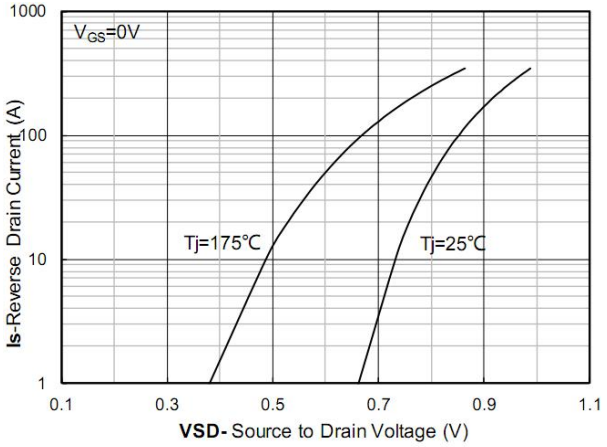


Figure 8. Forward characteristics of reverse diode; typical values

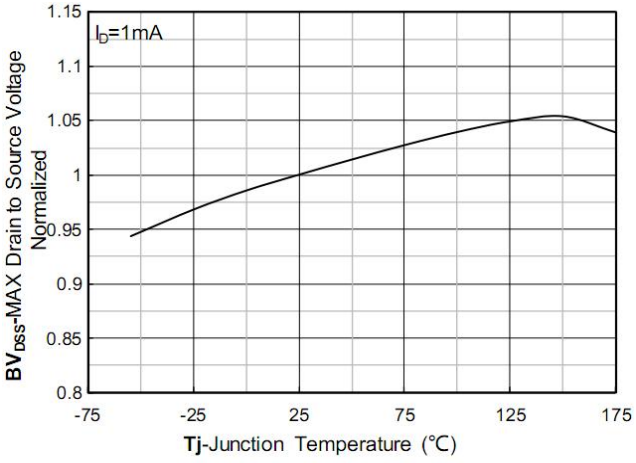


Figure 9. Normalized breakdown voltage

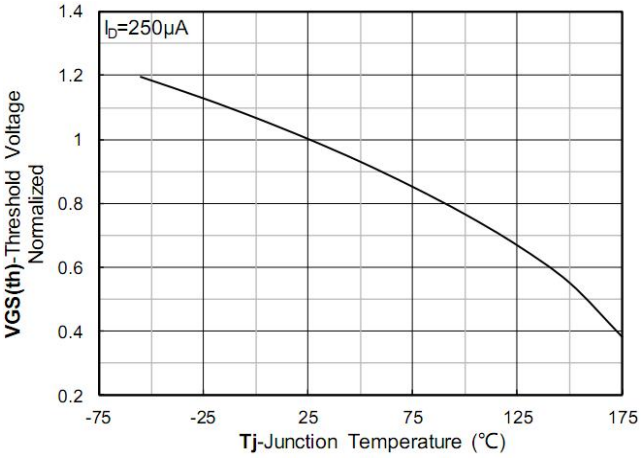


Figure 10. Normalized Threshold voltage

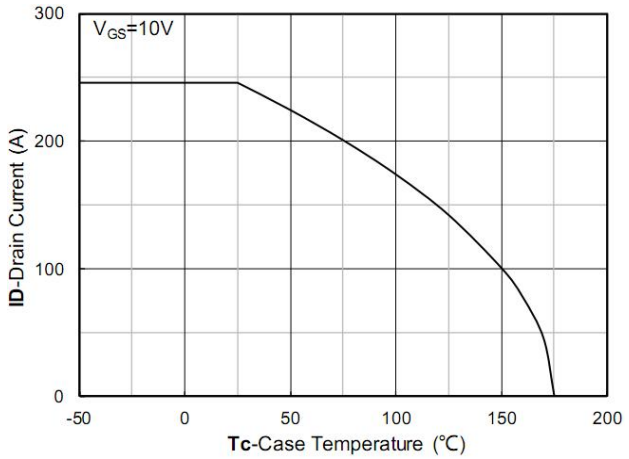


Figure 11. Current dissipation

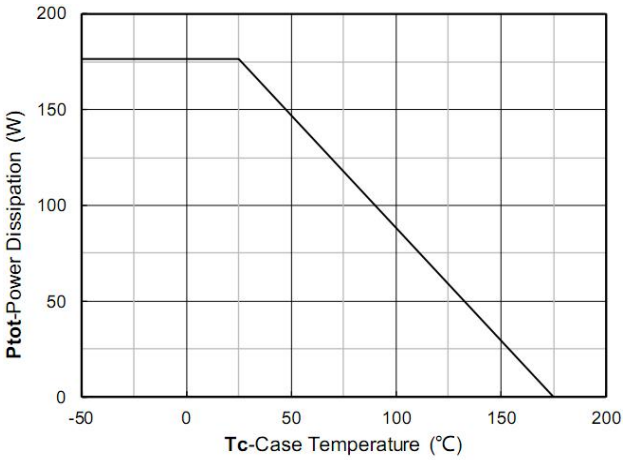


Figure 12. Power dissipation

Typical Characteristics

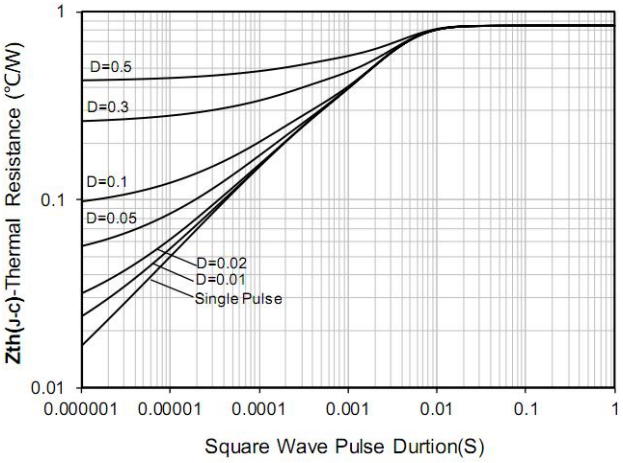


Figure 13. Maximum Transient Thermal Impedance

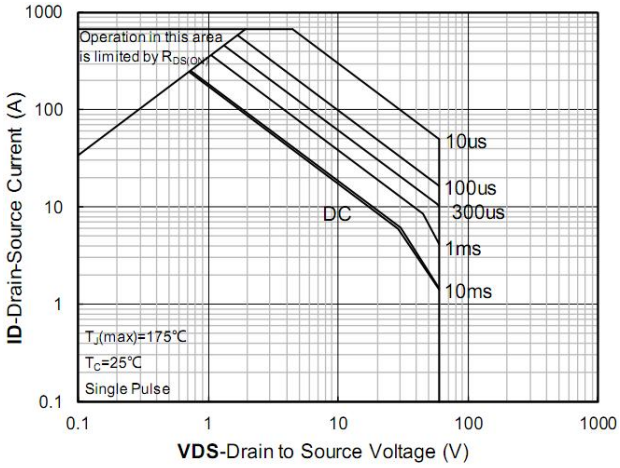
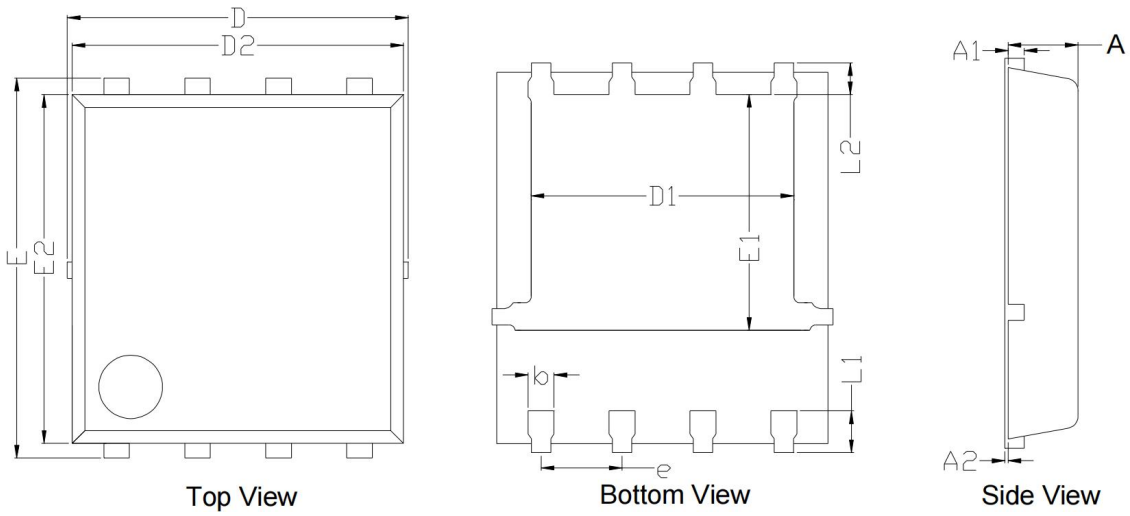


Figure 14. Safe Operation Area

PDFN5*6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
D	5.150	5.550	0.203	0.219
E	5.950	6.150	0.234	0.242
A	0.850	1.050	0.033	0.041
A1	0.203 BSC.		0.008 BSC.	
A2	0.000	0.080	0.000	0.003
D1	4.250	4.450	0.167	0.175
E1	3.525	3.725	0.139	0.147
D2	5.200 REF.		0.205 REF.	
E2	5.550 REF.		0.219 REF.	
L1	0.450	0.650	0.018	0.026
L2	0.680 BSC.		0.027 BSC.	
b	0.300	0.500	0.012	0.020
e	1.270 BSC.		0.050 BSC.	